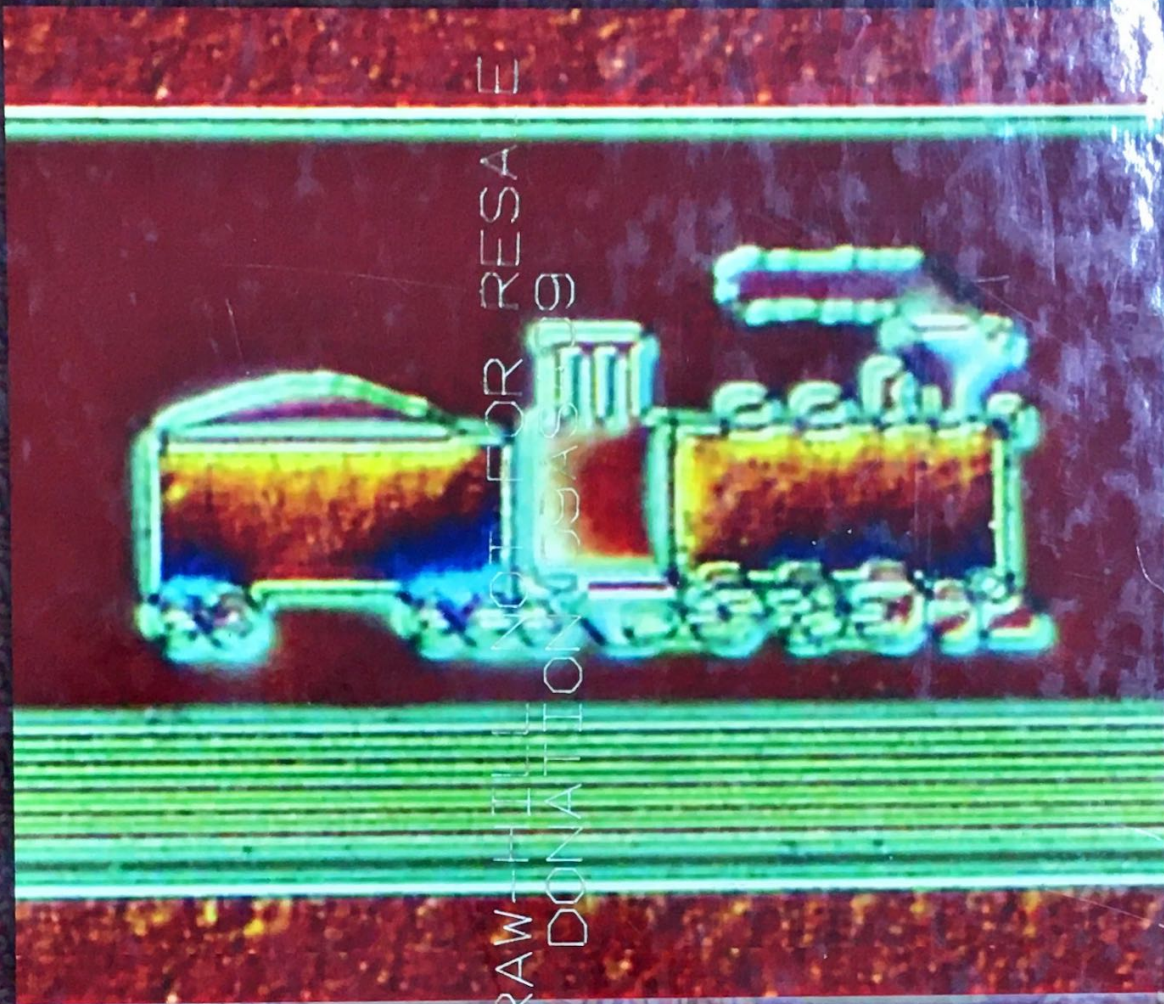


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Richard C. Jaeger
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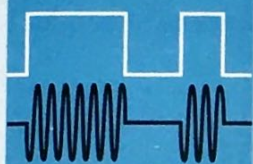
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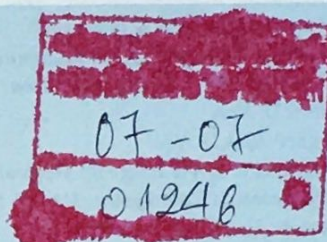
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MICROELECTRONIC CIRCUIT DESIGN

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